









	<p>FQB34N20LTM</p>
	<p>Hersteller-Teilenummer: FQB34N20LTM</p> <p>Hersteller / Marke: AMI Semiconductor / ON Semiconductor</p> <p>Teil der Beschreibung: MOSFET N-CH 200V 31A D2PAK</p> <p>Datenblätter:  FQB34N20LTM.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 32708 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
	
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	FQB34N20LTM
Hersteller	AMI Semiconductor / ON Semiconductor
Beschreibung	MOSFET N-CH 200V 31A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	32708 pcs Stock
Hersteller Standard Vorlaufzeit	8 Weeks
detaillierte Beschreibung	N-Channel 200V 31A (Tc) 3.13W (Ta), 180W (Tc)
Serie	QFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D ² PAK (TO-263AB)
Verlustleistung (max)	3.13W (Ta), 180W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	200V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	31A (Tc)
Rds On (Max) @ Id, Vgs	75 mOhm @ 15.5A, 10V
VGS (th) (Max) @ Id	2V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	72nC @ 5V
Eingabekapazität (Ciss) (Max) @ Vds	3900pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	5V, 10V
Vgs (Max)	±20V
Verpackung	Cut Tape (CT)
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	FQB34N20LTM-ND











































FQB34N20LTM ist neu im Original, Suche FQB34N20LTM Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie FQB34N20LTM AMI Semiconductor / ON Semiconductor mit Garantie und Vertrauen. Anfrage FQB34N20LTM: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>FQB34P10 FAIRCHI FQB34P10 FAIRCHI</p>	 <p>FQB34N20L FAIRCHI FQB34N20L FAIRCHI</p>	 <p>FQB34N20 F FQB34N20 F</p>	 <p>FQB34N20TM-AM002 AMI Semiconductor / ON Semiconductor MOSFET N-CH 200V 31A D2PAK</p>
 <p>FQB34N20TM FAIRCHILD FQB34N20TM FAIRCHILD</p>	 <p>FQB34N20LTM Fairchild/ON Semiconductor MOSFET N-CH 200V 31A D2PAK</p>	 <p>FQB34N20TM_AM002 Fairchild/ON Semiconductor FQB34N20TM_AM002 Fairchild/ON Semiconductor</p>	 <p>FQB33N10TM AMI Semiconductor / ON Semiconductor MOSFET N-CH 100V 33A D2PAK</p>

heiße Teile

Mehr

 FQB2NA90TM	 FQB2P25TM	 FQB2P25TM	 FQB30N06	 FQB30N06L
 FQB30N06LTM	 FQB30N06LTM	 FQB30N06TM	 FQB30N06TM	 FQB32N12V2
 FQB32N12V2TM	 FQB32N12V2TM	 FQB32N20	 FQB32N20C	 FQB32N20CTM
 FQB32N20CTM	 FQB32N30	 FQB33N10	 FQB33N10L	 FQB33N10LTM
 FQB33N10LTM	 FQB33N10TM	 FQB33N10TM	 FQB34N20	 FQB34N20L
 FQB34N20LTM	 FQB34N20TM	 FQB34N20TM_AM002	 FQB34P10	 FQB34P10TM
 FQB34P10TM	 FQB34P10TM_F085	 FQB3N25TM	 FQB3N25TM	 FQB3N30TM
 FQB3N30TM	 FQB3N40TM	 FQB3N40TM	 FQB3N60C	 FQB3N80TM
 FQB3N80TM	 FQB3N90TM	 FQB3N90TM	 FQB3P20TM	 FQB3P20TM
 FQB3P50TM	 FQB3P50TM	 FQB44N10	 FQB44N10TM	 FQB44N10TM

Contact us: Info@Y-IC.com

HINZUFÜGEN: Einheit A5-B5 Nr.509, 5 / F Sing Win Fabrikgebäude, 15-17 Shing Yip St, Kwun Tong, Kowloon, HongKong.

Copyright © 2019 YIC International Co., Limited

